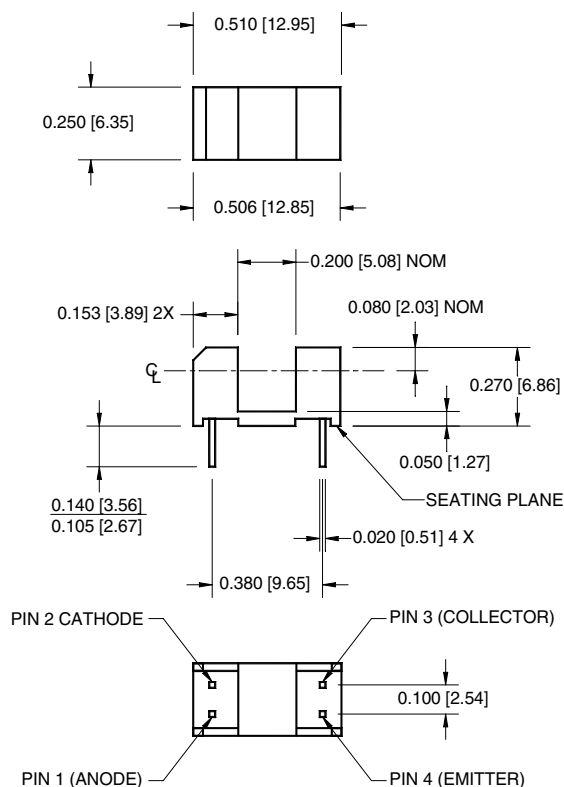


MOC70P1 / MOC70P2 / MOC70P3

PHOTOTRANSISTOR OPTICAL INTERRUPTER SWITCH

PACKAGE DIMENSIONS

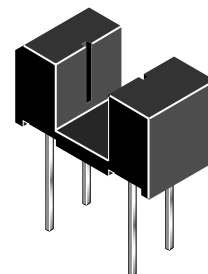


NOTES:

- Dimensions for all drawings are in inches (millimeters).
- Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.

DESCRIPTION

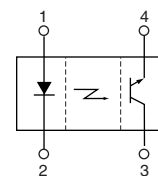
The MOC70PX consists of an infrared light emitting diode coupled to an NPN silicon phototransistor packaged into an injection molded housing. The housing is designed for wide gap, non contact sensing.



FEATURES

- No contact sensing
- 5 mm gap
- .040" aperture
- Low profile
- PCB mount
- Transistor output

SCHEMATIC



NOTES

- Derate power dissipation linearly, on each component, 1.67 mW/°C above 25°C.
- RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- Soldering iron tip 1/16" (1.6mm) from housing.
- As long as leads are not under any stress or spring tension.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Units
Operating Temperature	T_{OPR}	-55 to +100	°C
Storage Temperature	T_{STG}	-55 to +100	°C
Soldering Temperature (Iron) ^(2,3,4,5)	T_{SOL-I}	240 for 5 sec	°C
Soldering Temperature (Flow) ^(2,3,5)	T_{SOL-F}	260 for 10 sec	°C
EMITTER			
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	6	V
Power Dissipation ⁽¹⁾	P_D	100	mW
SENSOR			
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector Voltage	V_{ECO}	4.5	V
Collector Current	I_C	20	mA
Power Dissipation ⁽¹⁾	P_D	150	mW

MOC70P1 / MOC70P2 / MOC70P3

PHOTOTRANSISTOR OPTICAL INTERRUPTER SWITCH

ELECTRICAL / OPTICAL CHARACTERISTICS (T _A = 25°C)						
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
EMITTER						
Forward Voltage	I _F = 50 mA	V _F	—	—	1.8	V
Reverse Leakage Current	V _R = 6 V	I _R	—	—	100	μA
SENSOR						
Collector-Emitter Breakdown Voltage	I _C = 10 mA	BV _{CEO}	30	—	—	V
Emitter-Collector Breakdown Voltage	I _E = 100 μA	BV _{ECO}	4	—	—	V
Collector-Emitter Leakage	V _{CE} = 10 V, I _F = 0	I _{CEO}	—	—	100	nA
COUPLED						
Collector Current (See selection guide below)		I _{C(ON)}				
Collector Emitter Saturation Voltage (See selection guide below)		V _{CE (SAT)}				
Turn-on Time	I _F = 30 mA, V _{CC} = 5 V, R _L = 2.5 kΩ	t _(ON)	—	20	—	μs
Turn-off Time	I _F = 30 mA, V _{CC} = 5 V, R _L = 2.5 kΩ	t _(OFF)	—	80	—	μs

MOC70PX OPTICAL SWITCH SELECTION GUIDE						
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
ON-STATE COLLECTOR CURRENT						
MOC70P1	I _F = 5 mA, V _{CE} = 10 V	I _{C(ON)}	0.15	—	—	mA
MOC70P2	I _F = 5 mA, V _{CE} = 10 V	I _{C(ON)}	0.30	—	—	mA
MOC70P3	I _F = 5 mA, V _{CE} = 10 V	I _{C(ON)}	0.60	—	—	mA
MOC70P1	I _F = 20 mA, V _{CE} = 10 V	I _{C(ON)}	1.0	—	—	mA
MOC70P2	I _F = 20 mA, V _{CE} = 10 V	I _{C(ON)}	2.0	—	—	mA
MOC70P3	I _F = 20 mA, V _{CE} = 10 V	I _{C(ON)}	4.0	—	—	mA
MOC70P1	I _F = 30 mA, V _{CE} = 10 V	I _{C(ON)}	1.9	—	—	mA
MOC70P2	I _F = 30 mA, V _{CE} = 10 V	I _{C(ON)}	3.0	—	—	mA
MOC70P3	I _F = 30 mA, V _{CE} = 10 V	I _{C(ON)}	5.5	—	—	mA
COLLECTOR-EMITTER SATURATION VOLTAGE						
MOC70P1	I _F = 1.8 mA, I _F = 30 mA	V _{CE (SAT)}	—	—	0.40	V
MOC70P2	I _F = 1.8 mA, I _F = 20 mA	V _{CE (SAT)}	—	—	0.40	V
MOC70P3	I _F = 1.8 mA, I _F = 20 mA	V _{CE (SAT)}	—	—	0.40	V

Fig. 1 Forward Current vs. Forward Voltage

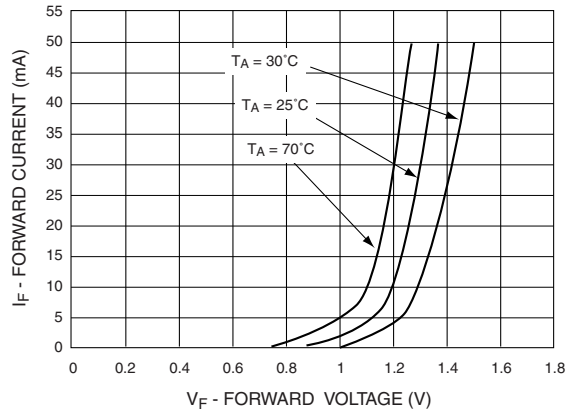


Fig. 2 Forward Voltage vs. Ambient Temperature

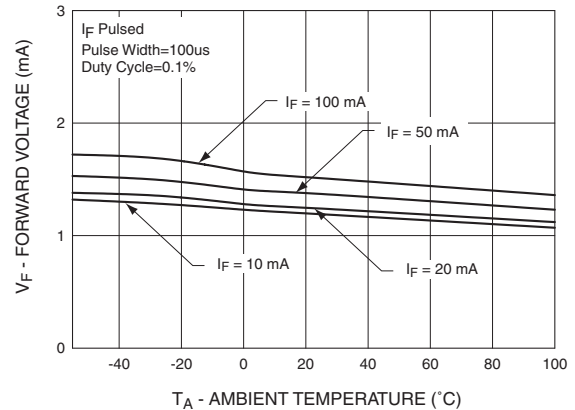


Fig. 3 Collector-Emitter Dark Current (Normalized) vs. Ambient Temperature

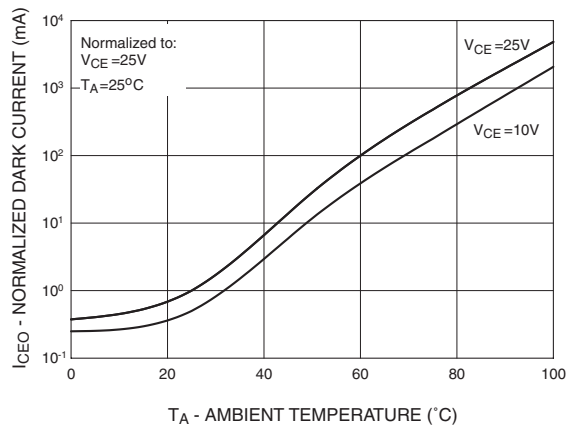
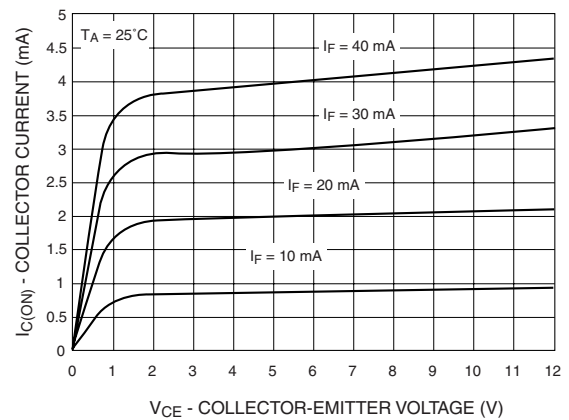
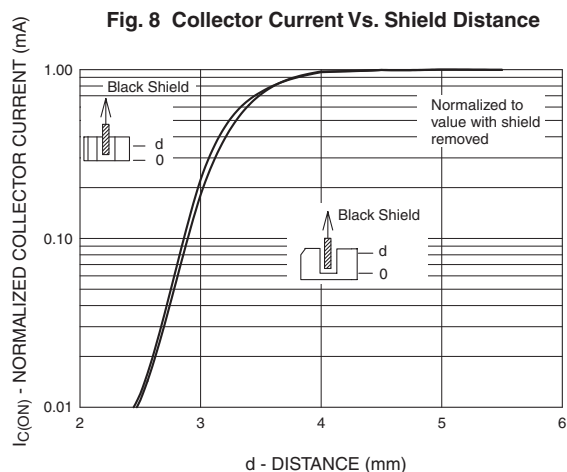
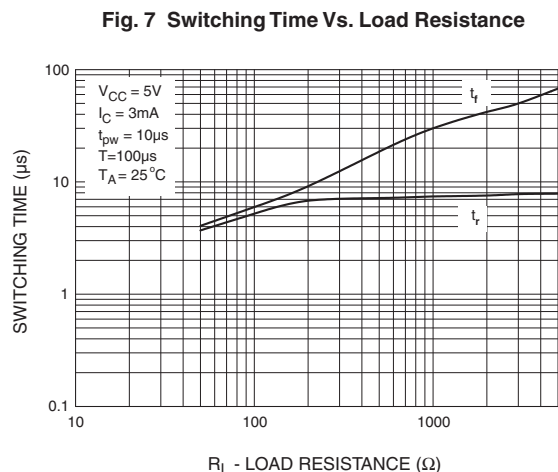
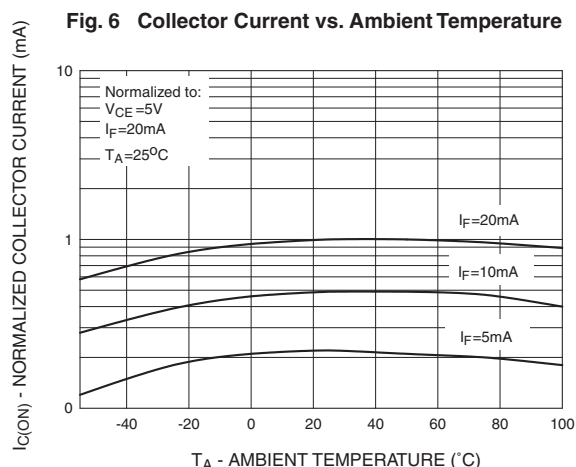
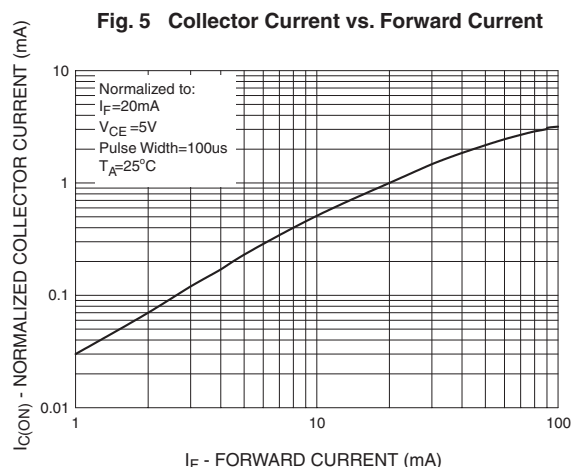
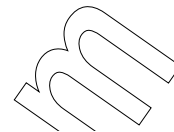


Fig. 4 Collector Current vs. Collector-Emitter Voltage





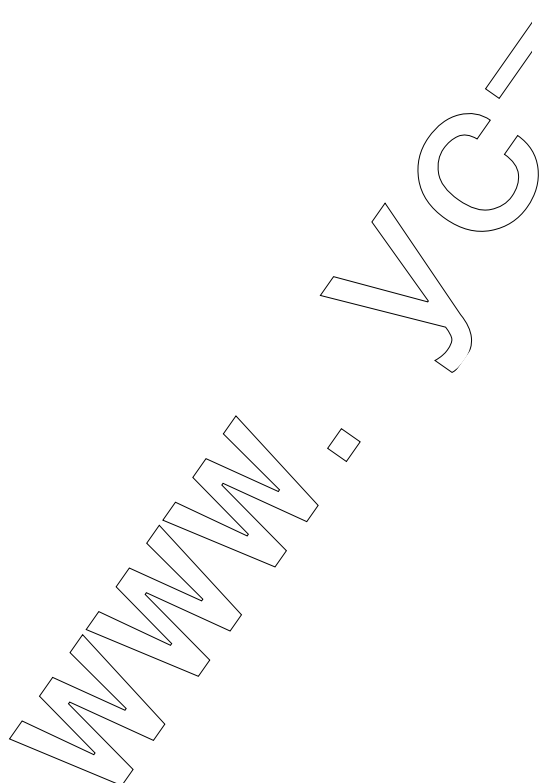


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